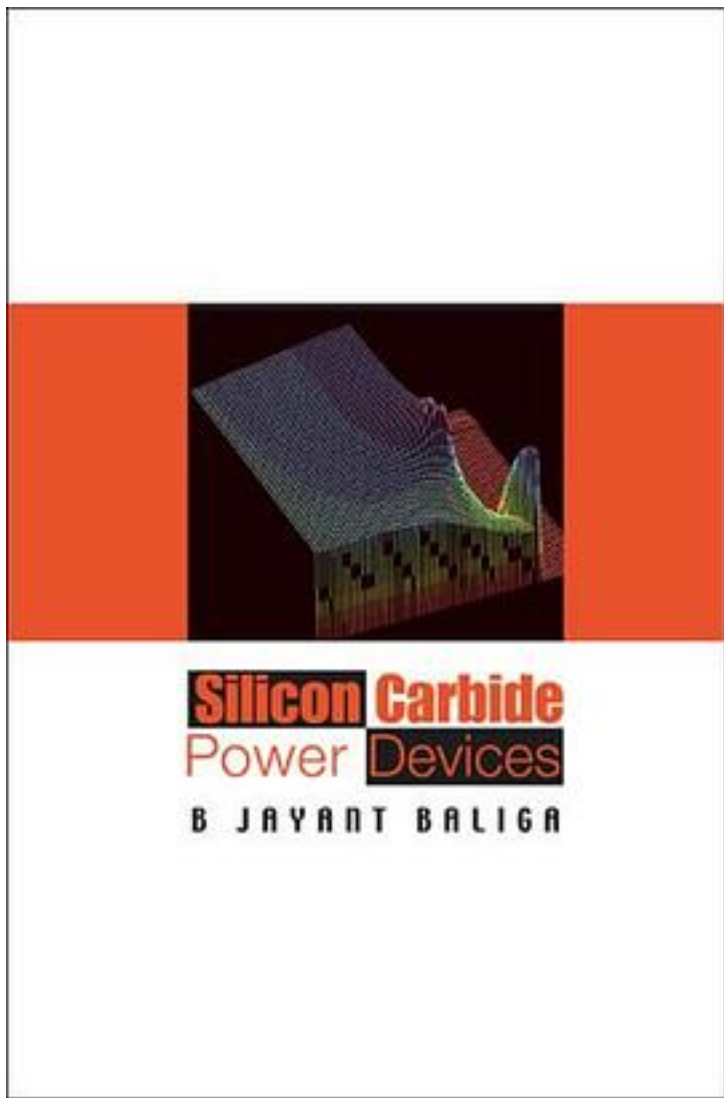


Silicon Carbide Power Devices



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著者:B. Jayant Baliga

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Power semiconductor devices are widely used for the control and management of electrical energy. The improving performance of power devices has enabled cost reductions and efficiency increases resulting in lower fossil fuel usage and less environmental pollution. This book provides the first cohesive treatment of the physics and design of silicon carbide power devices with an emphasis on unipolar structures. It uses the results of extensive numerical simulations to elucidate the operating principles of these important devices.

Contents: Material Properties and Technology; Breakdown Voltage; PiN Rectifiers; Schottky Rectifiers; Shielded Schottky Rectifiers; Metal-Semiconductor Field Effect Transistors; The Baliga-Pair Configuration; Planar Power MOSFETs; Shielded Planar MOSFETs; Trench-Gate Power MOSFETs; Shielded Trench-Gate MOSFETs; Charge Coupled Structures; Integral Diodes; Lateral High Voltage FETs; Synopsis.

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